

ABSTRACT

A semiconductor device includes a gate structure including a cell region and a contact region, a slit structure extending in a first direction through the gate structure, first channel structures disposed in the cell region of the gate structure, and second channel structures disposed in the cell region of the gate structure and disposed to be more adjacent to the contact region of the gate structure than the first channel structures. In a second direction that intersects the first direction, the first channel structures may be spaced apart from the slit structure by a first distance, and the second channel structures may be spaced apart from the slit structure at a second distance.

FIG. 1A